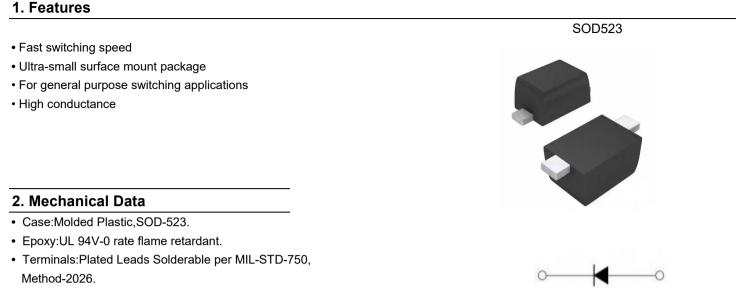


Silicon Epitaxial Planar Switching Diode



- Marking:T4
- Marking:marked on body.

3. Maximum Ratings

Electrical Characteristics Rating at 25°C ambient temperature unless otherwise specified.

Electrical Characteristics Rating at 25 C a		uniess otherwise spe	cilieu.	
Characteristic		Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage		V _{RM}	100	V
DC Blocking Voltage		V _R	75	V
Forward Continuous Current		I _F	150	mA
Repetitive peak forward current		I _{FRM}	250	mA
Non-Repetitive Peak Forward Current	@ t=1µs	I _{FSM}	2	A
	@ t=100ms		1	
Power Dissipation		P _D	150	mW
Thermal Resistance from Junction to Ambient Air		R _{eJA}	833	°C/W
Thermal Resistance from Junction to Ambient Case		R _{eJC}	561	°C/W
Junction Temperature		TJ	-55 to+150	°C
Storage Temperature Range		T _{stg}	-55 to+150	°C

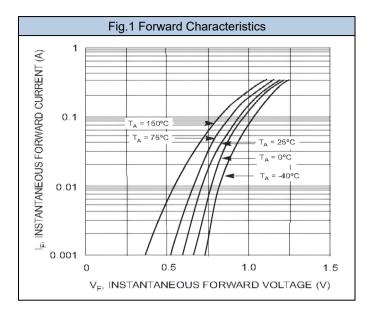
4. Electrical Characteristics (T_a=25 $^{\circ}$ C unless otherwise noted)

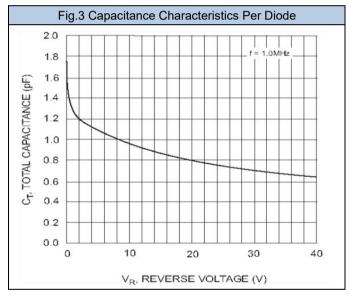
`````````````````````````````````		-				
Parameters	Symbol	Cindition	Min	TYP	Max	Unit
Reverse breakdown voltage	V _{BR}	Ι _R =1μΑ	75	-	-	V
		I _F = 1mA	-	-	0.715	mV
Forward Veltage	V	I _F = 10mA			0.855	
Forward Voltage	V _F	I _F = 50mA			1	
		l _F = 150mA			1.25	
		V _R = 75V	-	-	1	μA
Reverse Current		V _R = 20V			25	nA
	I _R	V _R = 75V T _J = 150℃			50	μA
		V _R = 25V T _J = 150℃			30	μA
Capacitance between terminals	CT	V _R = 0 V, f = 1 MHz			2	pF
Reverse Recovery Time	t _{rr}	I _F =I _R =10mA,I _{rr} =0.1*I _R , R _L =100Ω	-	-	4	ns

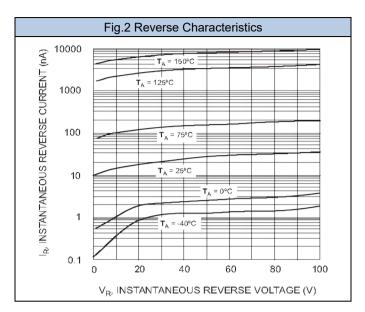


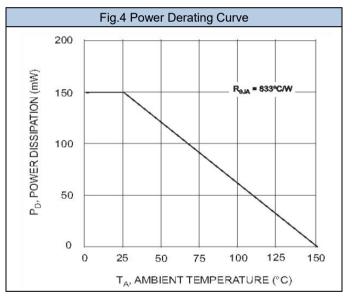
### Silicon Epitaxial Planar Switching Diode

### 5. Rating And Characteristic Curves





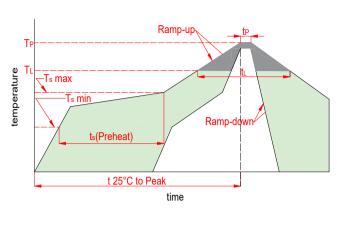






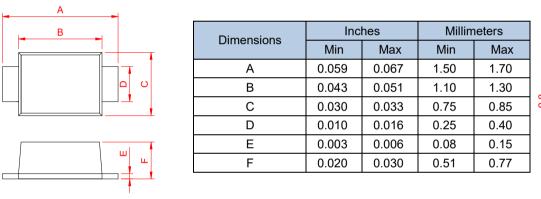
Silicon Epitaxial Planar Switching Diode

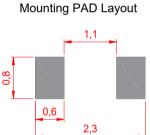
### 6. Soldering Parameters



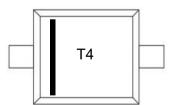
	Reflow Condition	Lead-free	
	Temp. min(T _s (min))	<b>150</b> ℃	
Pre Heat	Temp. max(T _s (min))	<b>200</b> ℃	
	Time(min to max)(t _s )	60~120s	
Aver. ramp	up rate(Liquidus Temp.)(T _L )to peak	3℃/s max	
T _s (max) to T _L -Ramp-up Rate		3℃/s max	
Reflow	Temp.(T _L )(Liquidus)	<b>217</b> ℃	
	Temp.(t _L )(Liquidus)	60~150s	
Peak Temp	.(T _P )	<b>260⁺⁰/-5°</b> ℃	
Time within	actual peak Temp.(t _p )	30s max	
Ramp-dowr	n Rate	6℃/s max	
Time 25°C to peak Tempe.( $T_p$ )		8 minutes max	
Do not exce	ed	<b>260</b> ℃	

### 7. Dimensions





### 8. Part Marking System



### 9. Package Information

Package	Туре	Tape Width (mm)	Quantity(pcs)
SOD523	1N4148WT	8	3000

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### Silicon Epitaxial Planar Switching Diode

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